UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 7,247,900 B2 Page 1 of 1

APPLICATION NO. : 10/631858 DATED : July 24, 2007 INVENTOR(S) : Honma et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title Page, item 56, under "References Cited" section, other References --Item I "Low Temperature Deposition Material" Section 4 "New Deposition Material" Ferroelectric Memory Advanced Process September 13, 1999-- should be added

Signed and Sealed this

Twenty-third Day of February, 2010

David J. Kappos Director of the United States Patent and Trademark Office